

## 1. General description

Planar passivated sensitive gate four quadrant triac in a SOT78 plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

## 2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

## 3. Applications

- General purpose motor controls
- General purpose switching

## 4. Quick reference data

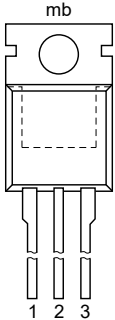
Table 1. Quick reference data

| Symbol                        | Parameter                            | Conditions                                                                                                             | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| $V_{DRM}$                     | repetitive peak off-state voltage    |                                                                                                                        | -   | -   | 800 | V    |
| $I_{T(RMS)}$                  | RMS on-state current                 | full sine wave; $T_{mb} \leq 107\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | -   | 4   | A    |
| $I_{TSM}$                     | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>  | -   | -   | 25  | A    |
|                               |                                      | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$                                                  | -   | -   | 27  | A    |
| $T_j$                         | junction temperature                 |                                                                                                                        | -   | -   | 125 | °C   |
| <b>Static characteristics</b> |                                      |                                                                                                                        |     |     |     |      |
| $I_{GT}$                      | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                     | -   | 2.5 | 10  | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                     | -   | 4   | 10  | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>                     | -   | 5   | 10  | mA   |

| Symbol                         | Parameter                         | Conditions                                                                                                                              | Min | Typ | Max | Unit             |
|--------------------------------|-----------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------------------|
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7                                       | -   | 11  | 25  | mA               |
| $I_H$                          | holding current                   | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 9                                                                         | -   | 2.2 | 15  | mA               |
| $V_T$                          | on-state voltage                  | $I_T = 5\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 10                                                                         | -   | 1.4 | 1.7 | V                |
| <b>Dynamic characteristics</b> |                                   |                                                                                                                                         |     |     |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage | $V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit | -   | 50  | -   | V/ $\mu\text{s}$ |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                    | Simplified outline                                                                                         | Graphic symbol                                                                                    |
|-----|--------|--------------------------------|------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------|
| 1   | T1     | main terminal 1                |  <p>TO-220AB (SOT78)</p> |  <p>sym051</p> |
| 2   | T2     | main terminal 2                |                                                                                                            |                                                                                                   |
| 3   | G      | gate                           |                                                                                                            |                                                                                                   |
| mb  | T2     | mounting base; main terminal 2 |                                                                                                            |                                                                                                   |

## 6. Ordering information

Table 3. Ordering information

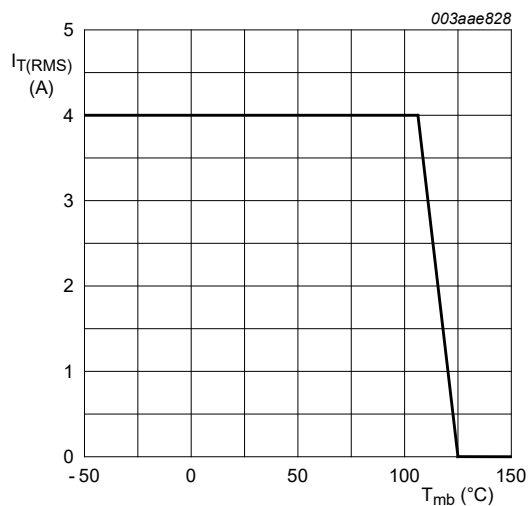
| Type number | Package  |                                                                                  |         |
|-------------|----------|----------------------------------------------------------------------------------|---------|
|             | Name     | Description                                                                      | Version |
| BT136-800E  | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |

## 7. Limiting values

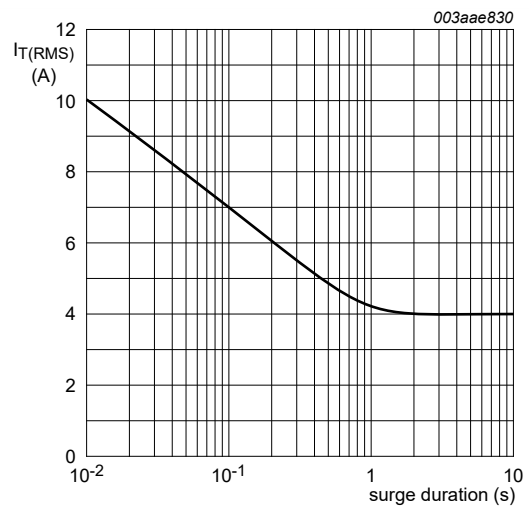
**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol              | Parameter                            | Conditions                                                                                                                                          | Min | Max | Unit                   |
|---------------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------------------------|
| $V_{\text{DRM}}$    | repetitive peak off-state voltage    |                                                                                                                                                     | -   | 800 | V                      |
| $I_{\text{T(RMS)}}$ | RMS on-state current                 | full sine wave; $T_{\text{mb}} \leq 107\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>         | -   | 4   | A                      |
| $I_{\text{TSM}}$    | non-repetitive peak on-state current | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | 25  | A                      |
|                     |                                      | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 16.7\text{ ms}$                                                 | -   | 27  | A                      |
| $I^2t$              | $I^2t$ for fusing                    | $t_{\text{p}} = 10\text{ ms}$ ; SIN                                                                                                                 | -   | 3.1 | $\text{A}^2\text{s}$   |
| $di_{\text{T}}/dt$  | rate of rise of on-state current     | $I_{\text{G}} = 20\text{ mA}$                                                                                                                       | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{G}} = 20\text{ mA}$                                                                                                                       | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{G}} = 20\text{ mA}$                                                                                                                       | -   | 50  | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{G}} = 50\text{ mA}$                                                                                                                       | -   | 10  | $\text{A}/\mu\text{s}$ |
| $I_{\text{GM}}$     | peak gate current                    |                                                                                                                                                     | -   | 2   | A                      |
| $P_{\text{GM}}$     | peak gate power                      |                                                                                                                                                     | -   | 5   | W                      |
| $P_{\text{G(AV)}}$  | average gate power                   | over any 20 ms period                                                                                                                               | -   | 0.5 | W                      |
| $T_{\text{stg}}$    | storage temperature                  |                                                                                                                                                     | -40 | 150 | $^{\circ}\text{C}$     |
| $T_{\text{j}}$      | junction temperature                 |                                                                                                                                                     | -   | 125 | $^{\circ}\text{C}$     |



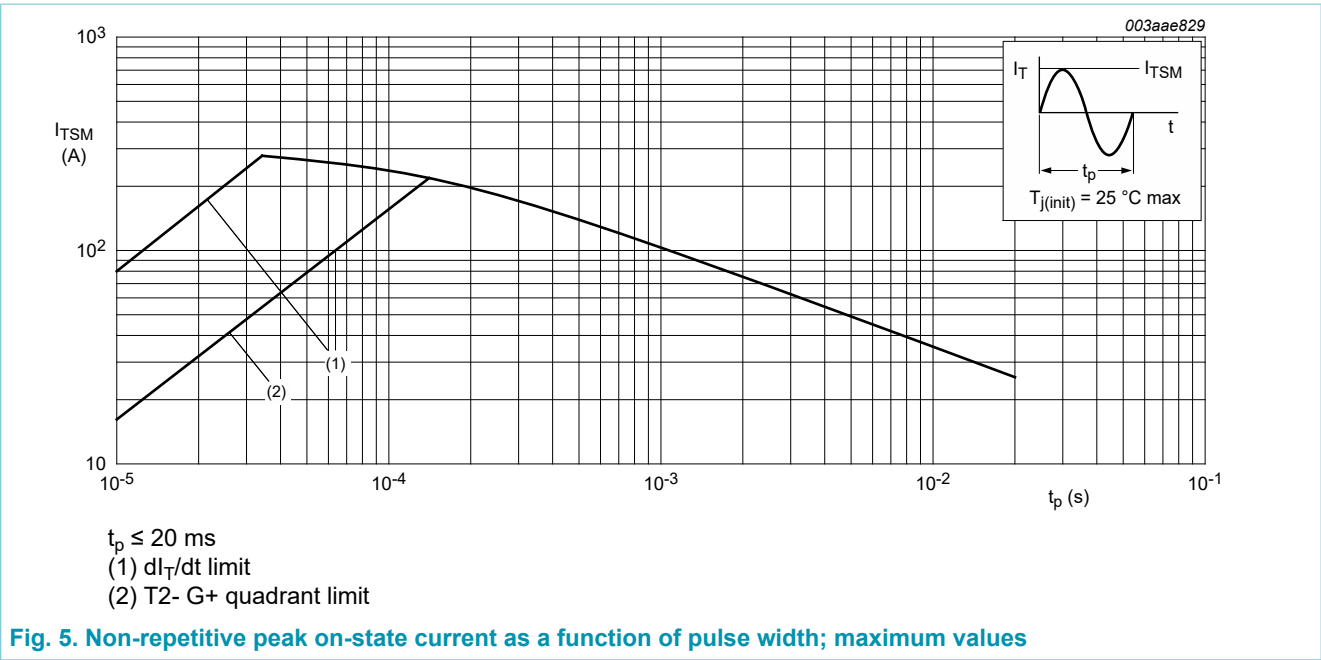
**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50\text{ Hz}$   
 $T_{\text{mb}} \leq 107\text{ }^{\circ}\text{C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**





8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter                                            | Conditions         |  | Min | Typ | Max | Unit |
|----------------|------------------------------------------------------|--------------------|--|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base    | half cycle; Fig. 6 |  | -   | -   | 3.7 | K/W  |
|                |                                                      | full cycle; Fig. 6 |  | -   | -   | 3   | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient free air | in free air        |  | -   | 60  | -   | K/W  |

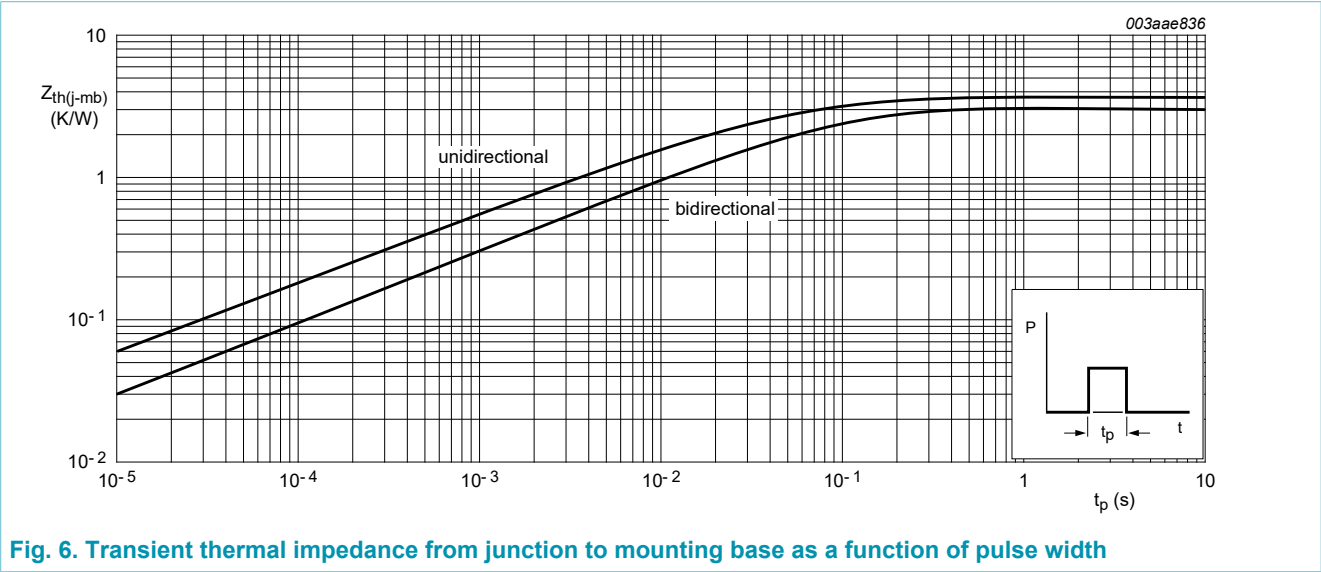
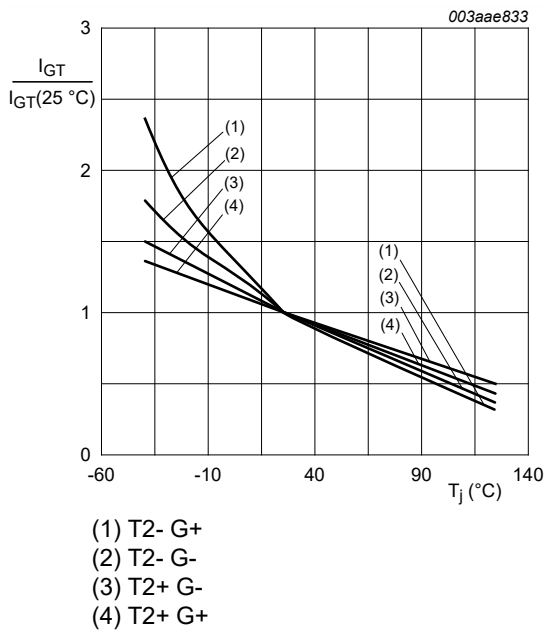


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

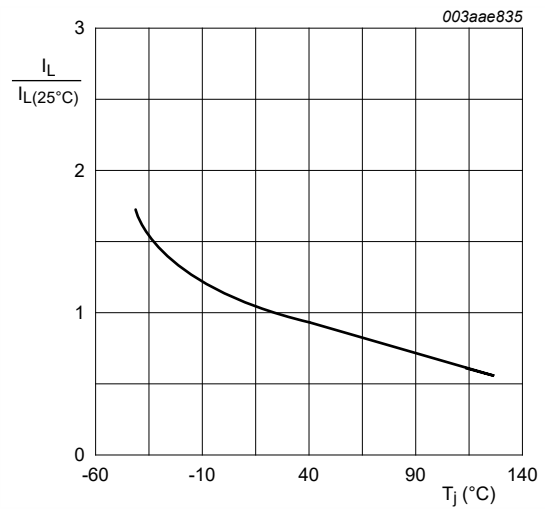
## 9. Characteristics

Table 6. Characteristics

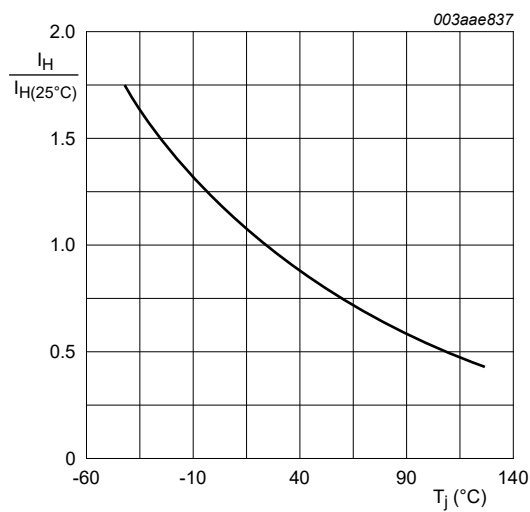
| Symbol                         | Parameter                         | Conditions                                                                                                                              | Min  | Typ | Max | Unit             |
|--------------------------------|-----------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------|------|-----|-----|------------------|
| <b>Static characteristics</b>  |                                   |                                                                                                                                         |      |     |     |                  |
| $I_{GT}$                       | gate trigger current              | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       | -    | 2.5 | 10  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       | -    | 4   | 10  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       | -    | 5   | 10  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                       | -    | 11  | 25  | mA               |
| $I_L$                          | latching current                  | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       | -    | 3   | 15  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       | -    | 10  | 20  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       | -    | 2.5 | 15  | mA               |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                       | -    | 4   | 20  | mA               |
| $I_H$                          | holding current                   | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>                                                         | -    | 2.2 | 15  | mA               |
| $V_T$                          | on-state voltage                  | $I_T = 5\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                                                         | -    | 1.4 | 1.7 | V                |
| $V_{GT}$                       | gate trigger voltage              | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>                              | -    | 0.7 | 1   | V                |
|                                |                                   | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>                            | 0.25 | 0.4 | -   | V                |
| $I_D$                          | off-state current                 | $V_D = 800\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$                                                                                | -    | 0.1 | 0.5 | mA               |
| <b>Dynamic characteristics</b> |                                   |                                                                                                                                         |      |     |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage | $V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit | -    | 50  | -   | V/ $\mu\text{s}$ |
| $t_{gt}$                       | gate-controlled turn-on time      | $I_{TM} = 6\text{ A}$ ; $V_D = 800\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$                                | -    | 2   | -   | $\mu\text{s}$    |



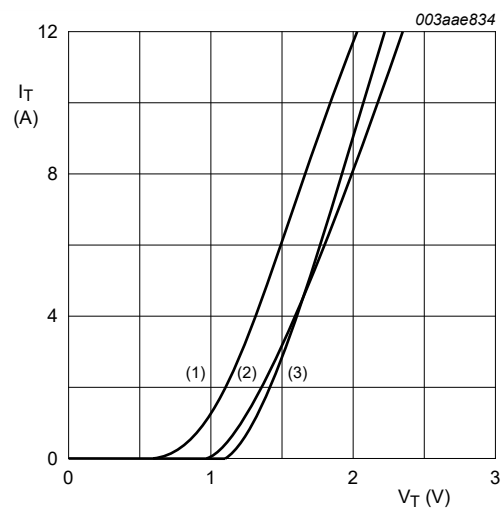
**Fig. 7. Normalized gate trigger current as a function of junction temperature**



**Fig. 8. Normalized latching current as a function of junction temperature**



**Fig. 9. Normalized holding current as a function of junction temperature**



$V_o = 1.27 V$

$R_s = 0.091 \Omega$

(1)  $T_J = 125^\circ\text{C}$ ; typical values

(2)  $T_J = 125^\circ\text{C}$ ; maximum values

(3)  $T_J = 25^\circ\text{C}$ ; maximum values

**Fig. 10. On-state current as a function of on-state voltage**



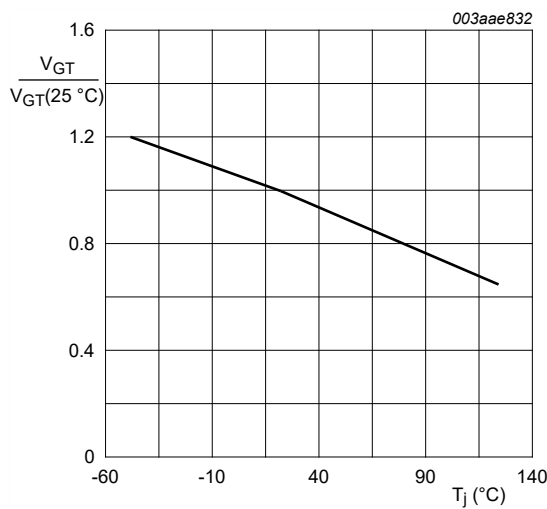


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

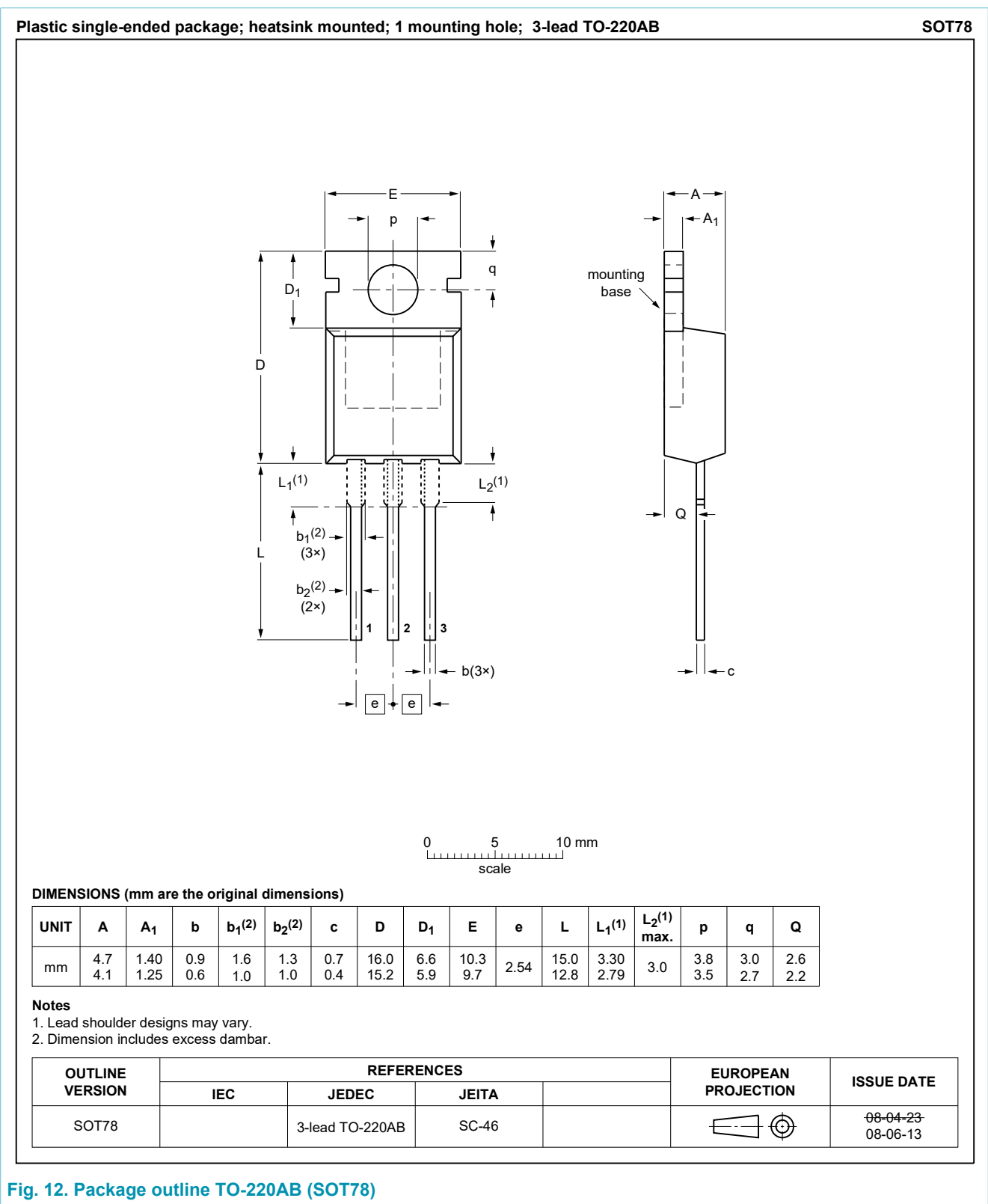


Fig. 12. Package outline TO-220AB (SOT78)

## 11. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 26 September 2018



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Электрон  
Связь**

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